



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _c = +25°C
100V	16mΩ @ V _{GS} = 10V	44A
	18mΩ @ V _{GS} = 6V	41A

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed

Description and Applications

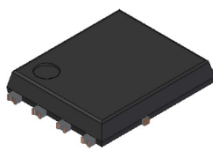
This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switches.

- Motor controls
- DC-DC converters
- Power management

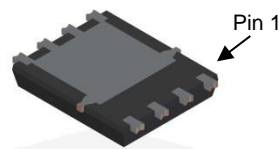
Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.097 grams (Approximate)

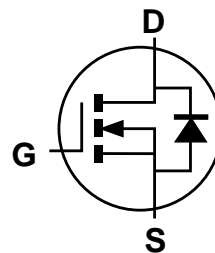
PowerDI5060-8/SWP (Type UX)



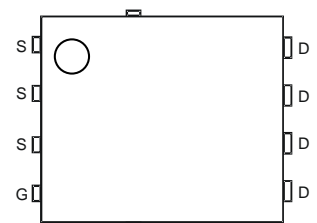
Top View



Bottom View



Internal Schematic



Top View
Pin Configuration

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	11 8	A
	Steady State	$T_C = +25^\circ\text{C}$ $T_C = +100^\circ\text{C}$	I_D	44 28	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	120	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	1.5	A
Avalanche Current (Note 6) $L = 3\text{mH}$			I_{AS}	7.5	A
Avalanche Energy (Note 6) $L = 3\text{mH}$			E_{AS}	85	mJ

Thermal Characteristics

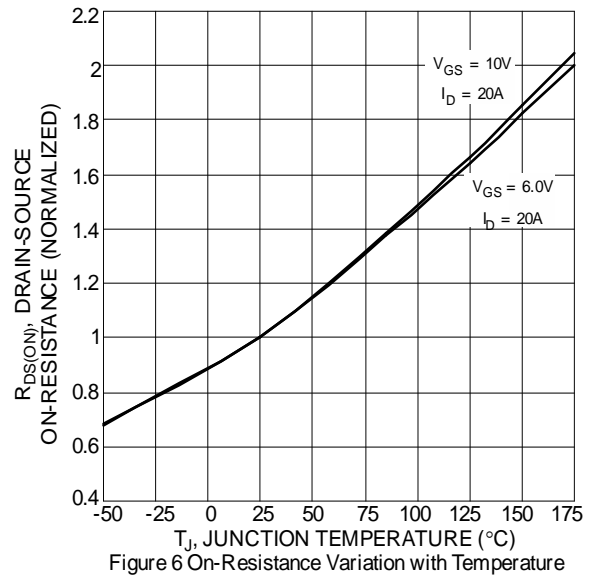
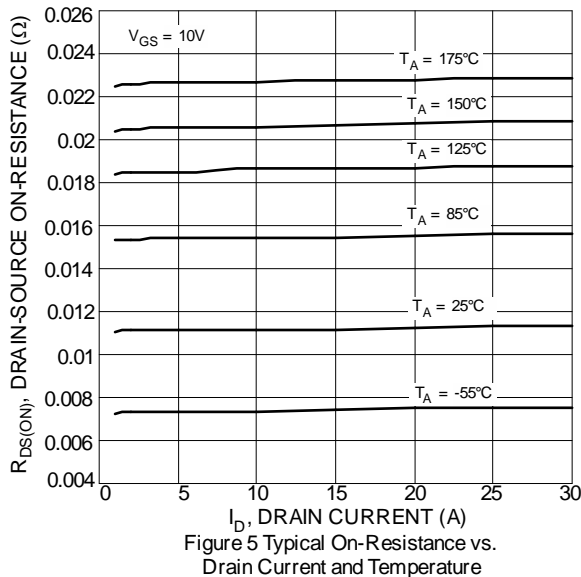
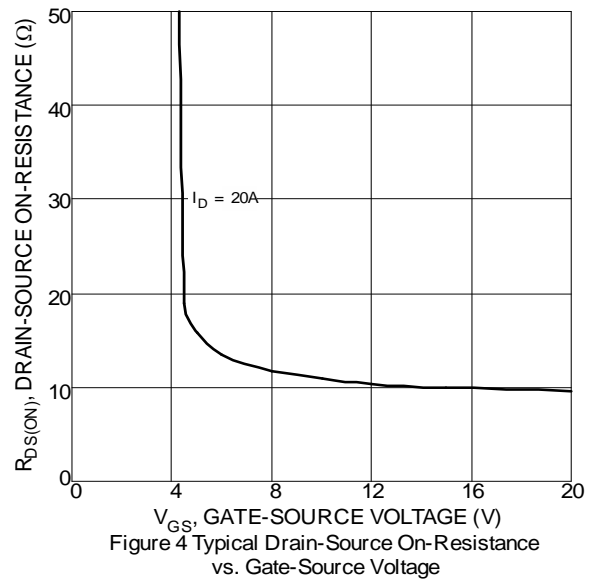
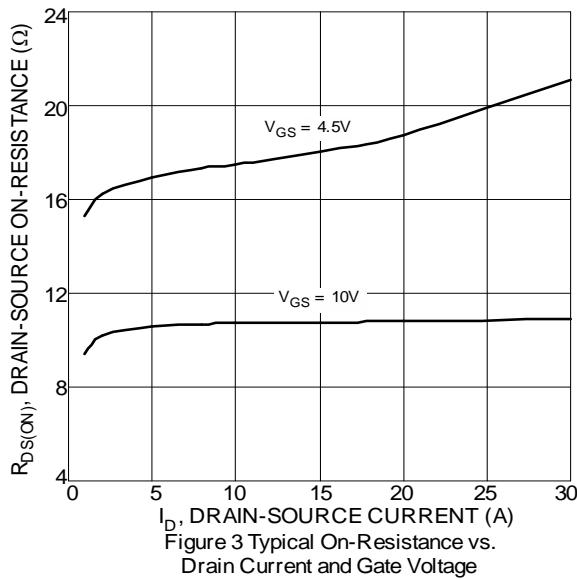
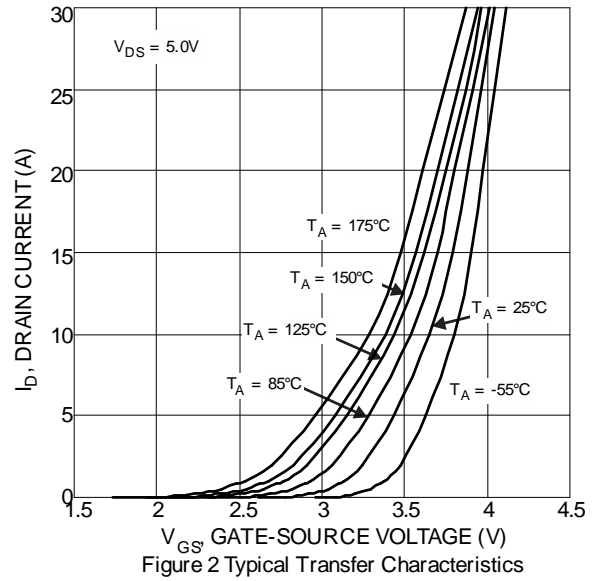
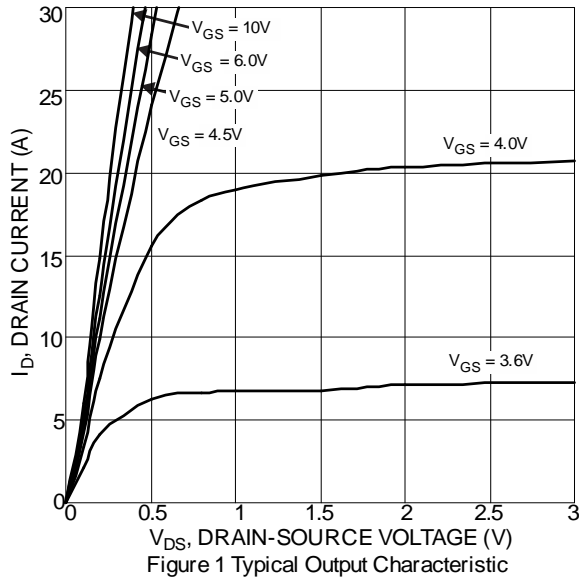
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	52	$^\circ\text{C/W}$
Total Power Dissipation	$T_C = +25^\circ\text{C}$	P_D	46	W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	2.7	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

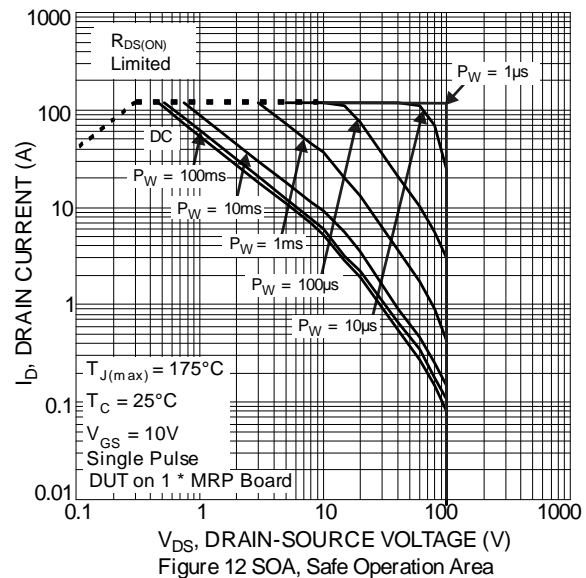
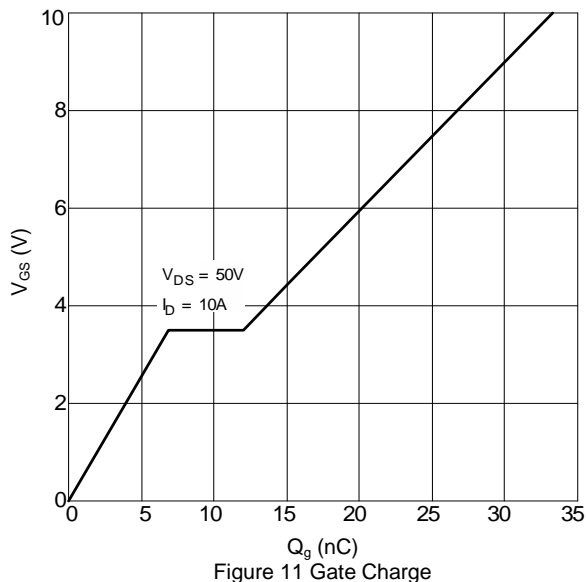
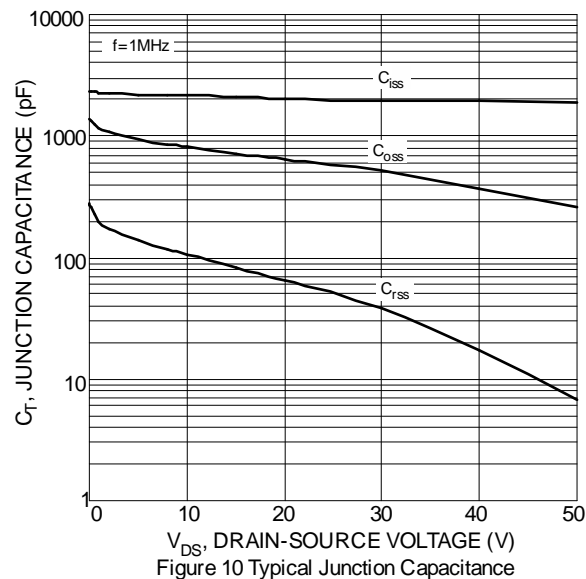
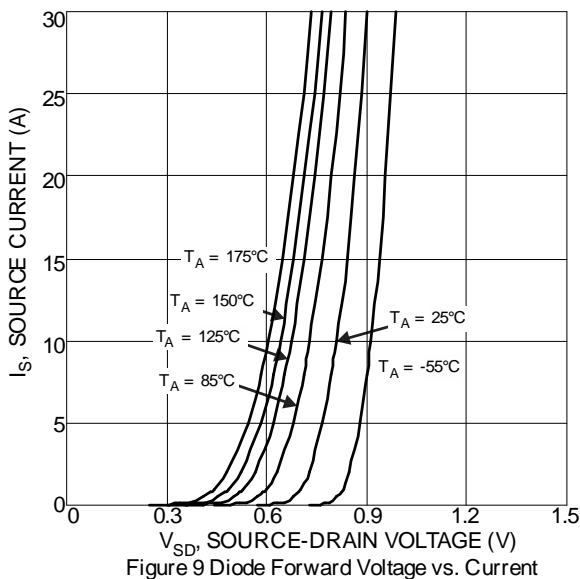
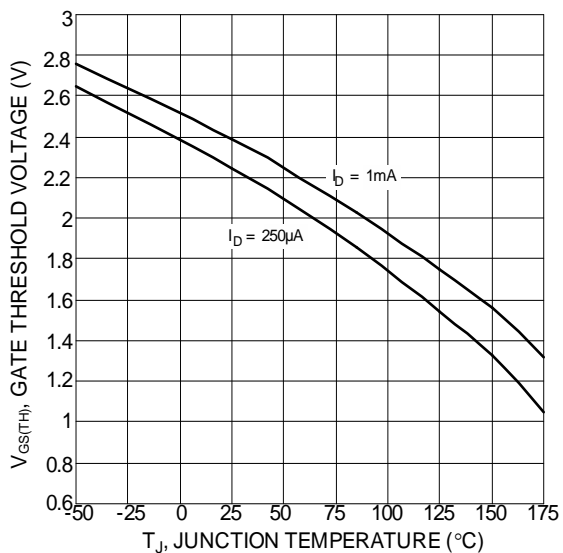
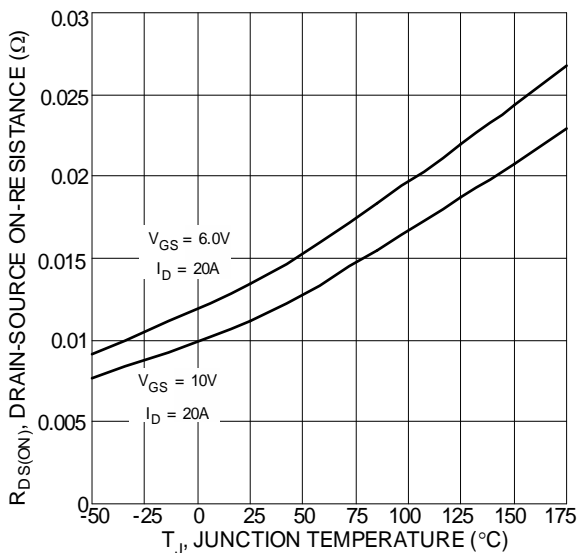
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 6. Guaranteed by design. Not subject to product testing.

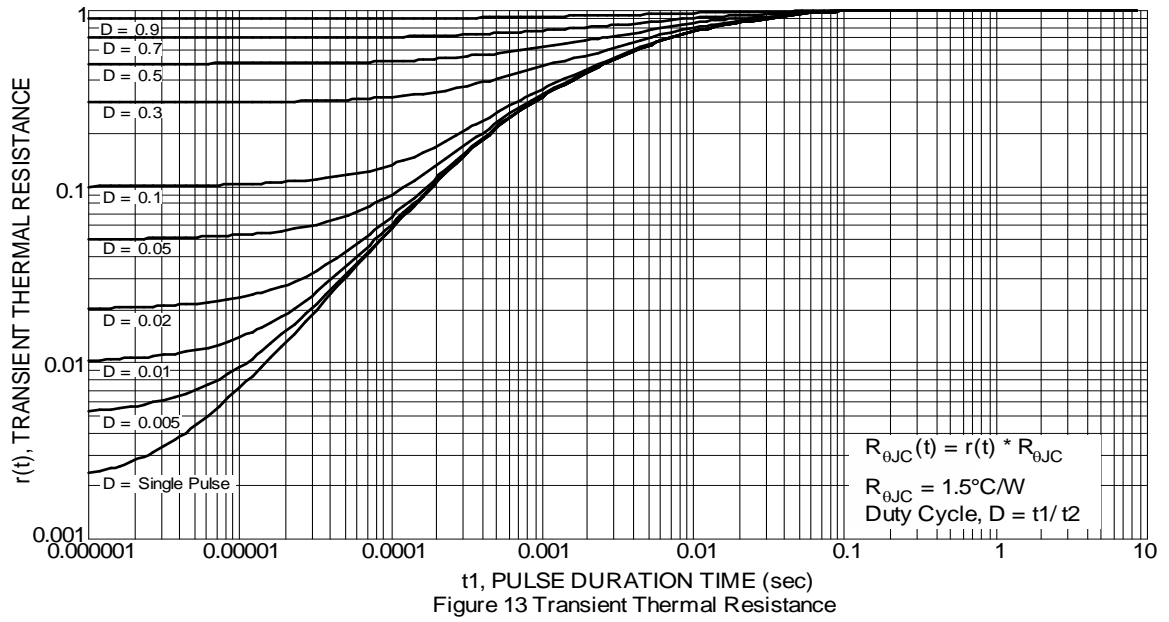
Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	$V_{GS} = 0V, I_D = 1mA$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 80V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.4	2	3	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	11	16	m Ω	$V_{GS} = 10V, I_D = 20A$
		—	13.5	18		$V_{GS} = 6V, I_D = 20A$
		—	18.4	25		$V_{GS} = 4.5V, I_D = 5A$
Diode Forward Voltage	V_{SD}	—	0.9	1.3	V	$V_{GS} = 0V, I_S = 20A$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	—	1,871	—	pF	$V_{DS} = 50V, V_{GS} = 0V$ $f = 1MHz$
Output Capacitance	C_{oss}	—	261	—		
Reverse Transfer Capacitance	C_{rss}	—	7	—		
Gate Resistance	R_g	—	0.75	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Q_g	—	33.3	—	nC	$V_{DD} = 50V, I_D = 10A$ $V_{GS} = 10V$
Gate-Source Charge	Q_{gs}	—	6.9	—		
Gate-Drain Charge	Q_{gd}	—	5.1	—		
Turn-On Delay Time	$t_{D(ON)}$	—	6.5	—	ns	$V_{DD} = 50V, V_{GS} = 10V$ $I_D = 10A, R_g = 6\Omega$
Turn-On Rise Time	t_r	—	7	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	19.7	—		
Turn-Off Fall Time	t_f	—	8.1	—		
Reverse Recovery Time	t_{RR}	—	37.9	—	ns	$I_F = 10A, di/dt = 100A/\mu s$
Reverse Recovery Charge	Q_{RR}	—	51.9	—	nC	

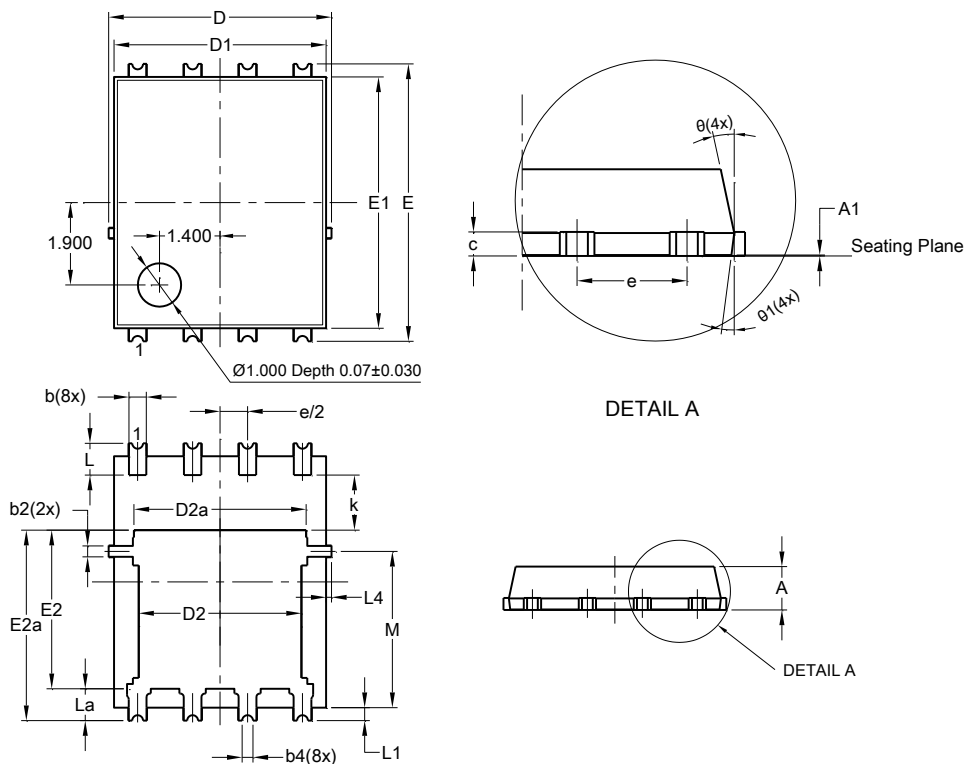
Notes: 6. Guaranteed by design. Not subject to product testing.
 7. Short duration pulse test used to minimize self-heating effect.





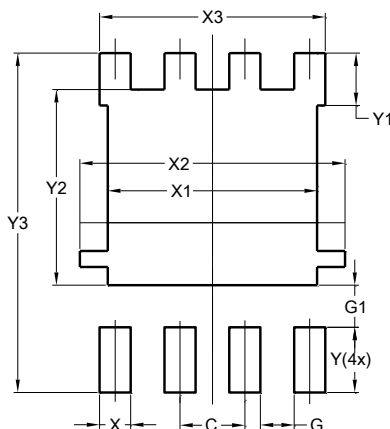


Package Outline Dimensions

PowerDI5060-8/SWP (Type UX)


PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

PowerDI5060-8/SWP (Type UX)


Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610